

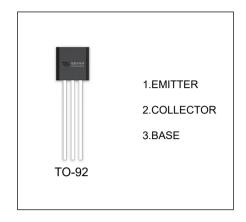
MPSH10 TRANSISTOR (NPN)

FEATURES

General Purpose Amplifier

APPLICATIONS

- In Low Noise UHF/VHF Amplifiers
- In Low Frequency Drift, High Output UHF Oscillators



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
MPSH10	TO-92	Bulk	1000pcs/Bag
MPSH10-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage	30	V	
V _{CEO}	Collector-Emitter Voltage	25	V	
V _{EBO}	Emitter-Base Voltage	3	V	
Ic	Collector Current -Continuous	40	mA	
P _D	Collector Power Dissipation	350	mW	
R _{θ JA}	Thermal Resistance rom Junction to Ambient	357	°C /W	
T_J , T_{stg}	Junction Temperature	-55~+150	℃	



Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 0.1mA,I _E =0	30			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA,I _B =0	25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =0.01mA,I _C =0	3			V
Collector cut-off current	I _{CBO}	V _{CB} =25V,I _E =0			0.1	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} =2V,I _C =0			0.1	μΑ
DC current gain	h _{FE(1)}	V _{CE} =10V, I _C =4mA	60			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =4mA,I _B =0.4mA			0.5	V
Base-emitter voltage	V _{BE}	I _C =4mA, V _{CE} =10V			0.95	V
Transition frequency	f _T	V _{CE} =10V,I _C =4mA,f=100MHz	650			MHz
Collector output capacitance	C _{cb}	V _{CB} =10V, I _E =0, f=1MHz			0.7	pF